RF-6.02 Plasma Source

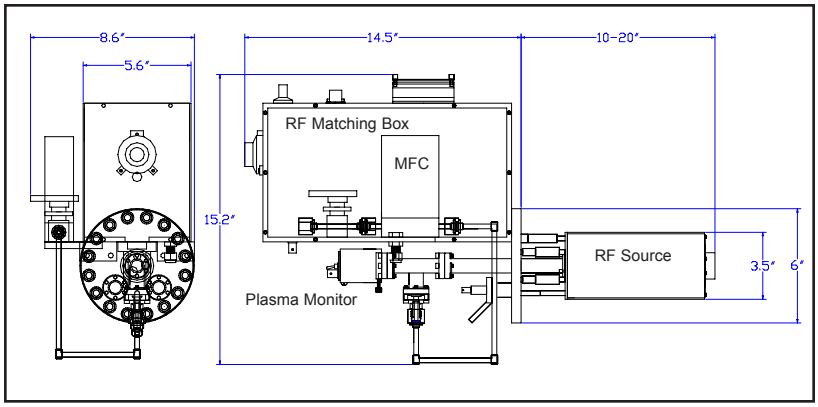
SVTA-RF-6.02

Features

- For N_2, O_2, and H_2
- Growth Rates Up to 6 μm/hr
- Flux Uniformity for Wafer Sizes Up to 8" Diameter
- Optical Port for Plasma Monitoring
- Custom Plasma Chamber and Apertures
- Automatic Tuning Matching Network
- Charge Suppression
- Fully Automated Plasma Source with Safety InterLock

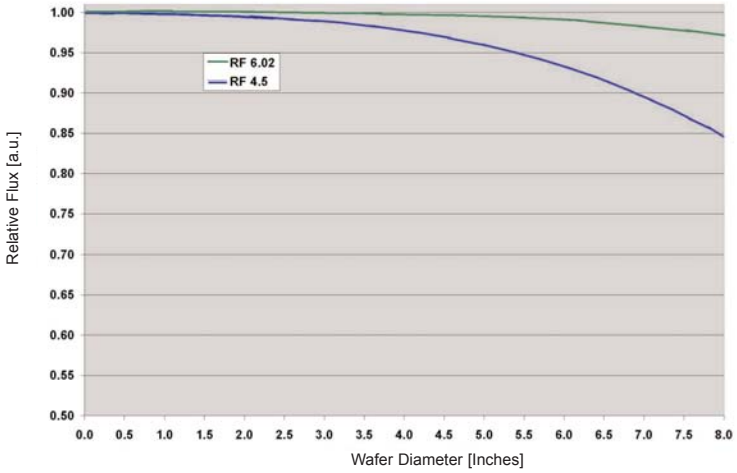
Description

The RF 6.02 is designed for high volume and large wafer size production systems for nitride and oxide thin film growth. The ROBO-RF PLASMA CONTROL SYSTEM allows fully automated operation of the RF plasma source with gas flow control and automatic RF matching network. The plasma control system provides information of the plasma status and operation parameters. The SVTA-RF-6.02 source shows superior flux uniformity for wafer sizes of 4" or larger. Due to it's robust mechanical and cooling water system design, growth rates as high as 6μm/hr or better can be achieved under optimal growth conditions.



Specifications

Operating RF Power Level.....200 - 1,200 Watts (US)
Gas Flow Rate.....0.1 - 10 sccm
Mounting Flange.....6.0" CFF
Source Diameter.....3.50" (89.25 mm)
Plasma Chamber.....PBN, Alumina
Source to Target Distance (Typical).....10.5"
Water Cooling.....0.5 GPM



Relative Flux Distribution of the SVTA-RF-4.5 and SVTA-RF-6.02

Model	Description
SVTA-RF-6.02PBN	PBN, Specify Length: 10" - 20"
SVTA-RF-6.02ALO	Alumina, Specify Length: 10" - 20"

Model	Optional Components
SVTA-RF-HVPS	High Voltage Supply for Charge Suppression Plates
SVTA-RF-RR	Robo RF Plasma Control System